

# SKM 75GB123D



**SEMITRANS® 2**

## IGBT Modules

SKM 75GB123D

SKM 75GAL123D

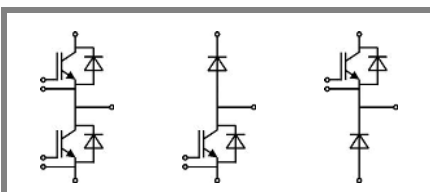
SKM 75GAR123D

### Features

- MOS input (voltage controlled)
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to  $6 \times I_{Cnom}$
- Latch-up free
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DCB Direct Copper Bonding Technology
- Large clearance (10 mm) and creepage distance (20 mm)

### Typical Applications\*

- AC inverter drives
- UPS



GB

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Absolute Maximum Ratings		$T_c = 25^\circ\text{C}$ , unless otherwise specified		
Symbol	Conditions	Values		Units
<b>IGBT</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$	1200		V
$I_C$	$T_j = 150^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$	75	A
		$T_{case} = 80^\circ\text{C}$	60	A
$I_{CRM}$	$I_{CRM} = 2 \times I_{Cnom}$	150		A
$V_{GES}$		$\pm 20$		V
$t_{psc}$	$V_{CC} = 600\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125^\circ\text{C}$ $V_{CES} < 1200\text{ V}$	10		$\mu\text{s}$
<b>Inverse Diode</b>				
$I_F$	$T_j = 150^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$	75	A
		$T_{case} = 80^\circ\text{C}$	50	A
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	150		A
$I_{FSM}$	$t_p = 10\text{ ms}; \sin.$	$T_j = 150^\circ\text{C}$	480	A
<b>Freewheeling Diode</b>				
$I_F$	$T_j = 150^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$	95	A
		$T_{case} = 80^\circ\text{C}$	65	A
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	200		A
$I_{FSM}$	$t_p = 10\text{ ms}; \sin$	$T_j = 150^\circ\text{C}$	720	A
<b>Module</b>				
$I_{t(RMS)}$		200		A
$T_{vj}$		- 40 ... + 150		$^\circ\text{C}$
$T_{stg}$		- 40 ... + 125		$^\circ\text{C}$
$V_{isol}$	AC, 1 min.	2500		V

Characteristics		$T_c = 25^\circ\text{C}$ , unless otherwise specified				
Symbol	Conditions	min.	typ.	max.	Units	
<b>IGBT</b>						
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 2\text{ mA}$	4,5	5,5	6,5	V	
$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$		0,1	0,3	mA	
$V_{CE0}$		$T_j = 25^\circ\text{C}$	1,4	1,6	V	
		$T_j = 125^\circ\text{C}$	1,6	1,8	V	
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	22	28	m $\Omega$	
		$T_j = 125^\circ\text{C}$	30	38	m $\Omega$	
$V_{CE(sat)}$	$I_{Cnom} = 50\text{ A}, V_{GE} = 15\text{ V}$		2,5	3	V	
$C_{ies}$	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$		3,3	nF	
$C_{oes}$			0,5	0,6	nF	
$C_{res}$			0,22	0,3	nF	
$Q_G$	$V_{GE} = -8 - +20\text{ V}$		500		nC	
$R_{Gint}$	$T_j = ^\circ\text{C}$		5		$\Omega$	
$t_{d(on)}$	$R_{Gon} = 22\ \Omega$	$V_{CC} = 600\text{ V}$ $I_C = 50\text{ A}$		44	100	ns
$t_r$				56	100	ns
$E_{on}$				8		mJ
$t_{d(off)}$	$R_{Goff} = 22\ \Omega$	$T_j = 125^\circ\text{C}$ $V_{GE} = \pm 15\text{ V}$		380	500	ns
$t_f$				70	100	ns
$E_{off}$				5		mJ
$R_{th(j-c)}$	per IGBT			0,27	K/W	

# SKM 75GB123D



**SEMITRANS® 2**

## IGBT Modules

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SKM 75GAL123D

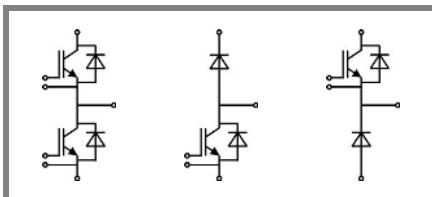
SKM 75GAR123D

### Features

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Characteristics				min.	typ.	max.	Units
<b>Inverse Diode</b>							
$V_F = V_{EC}$	$I_{Fnom} = 50 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$		2		2,5	V
		$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$		1,8			V
$V_{F0}$		$T_j = 25 \text{ }^\circ\text{C}$		1,1		1,2	V
		$T_j = 125 \text{ }^\circ\text{C}$					V
$r_F$		$T_j = 25 \text{ }^\circ\text{C}$		18		26	mΩ
		$T_j = 125 \text{ }^\circ\text{C}$					mΩ
$I_{RRM}$	$I_F = 50 \text{ A}$	$T_j = 125 \text{ }^\circ\text{C}$		35			A
$Q_{rr}$	$di/dt = 800 \text{ A}/\mu\text{s}$						μC
$E_{rr}$	$V_{GE} = 0 \text{ V}; V_{CC} = 600 \text{ V}$						mJ
$R_{th(j-c)D}$	per diode					0,6	K/W
<b>Freewheeling Diode</b>							
$V_F = V_{EC}$	$I_{Fnom} = 50 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$		1,85		2,2	V
		$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$		1,6			V
$V_{F0}$		$T_j = 25 \text{ }^\circ\text{C}$		1,1		1,2	V
		$T_j = 125 \text{ }^\circ\text{C}$					V
$r_F$		$T_j = 25 \text{ }^\circ\text{C}$		15		20	V
		$T_j = 125 \text{ }^\circ\text{C}$					V
$I_{RRM}$	$I_F = 50 \text{ A}$	$T_j = 125 \text{ }^\circ\text{C}$		40			A
$Q_{rr}$							μC
$E_{rr}$	$V_{GE} = 0 \text{ V}; V_{CC} = 600 \text{ V}$						mJ
$R_{th(j-c)FD}$	per diode					0,5	K/W
<b>Module</b>							
$L_{CE}$						30	nH
$R_{CC'+EE'}$	res., terminal-chip	$T_{case} = 25 \text{ }^\circ\text{C}$		0,75			mΩ
		$T_{case} = 125 \text{ }^\circ\text{C}$		1			mΩ
$R_{th(c-s)}$	per module					0,05	K/W
$M_s$	to heat sink M6			3		5	Nm
$M_t$	to terminals M5			2,5		5	Nm
w						160	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

# SKM 75GB123D



**SEMITRANS<sup>®</sup> 2**

## IGBT Modules

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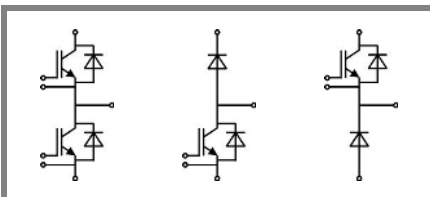
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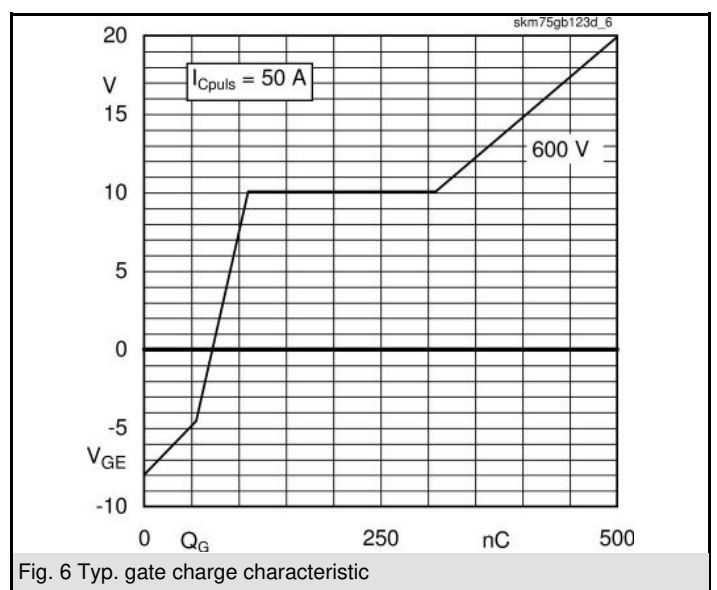
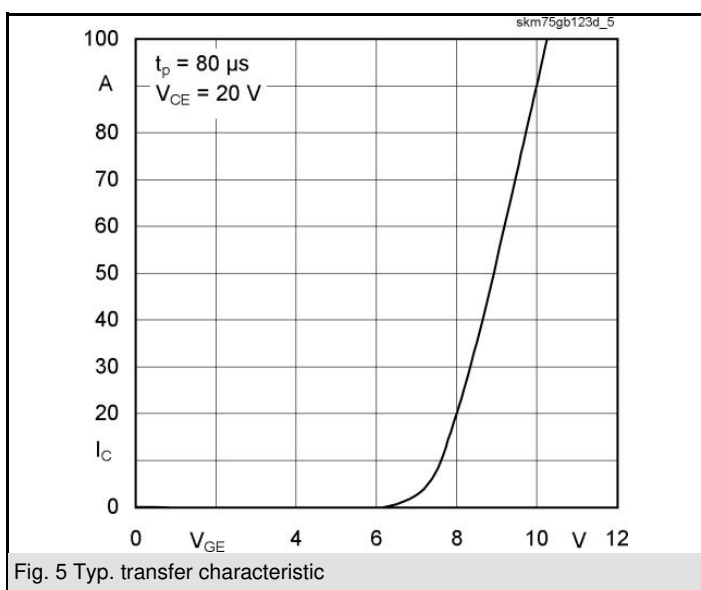
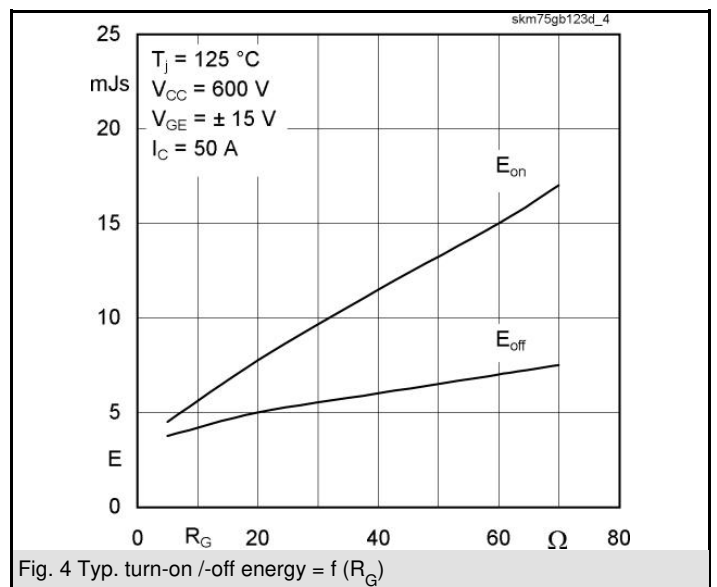
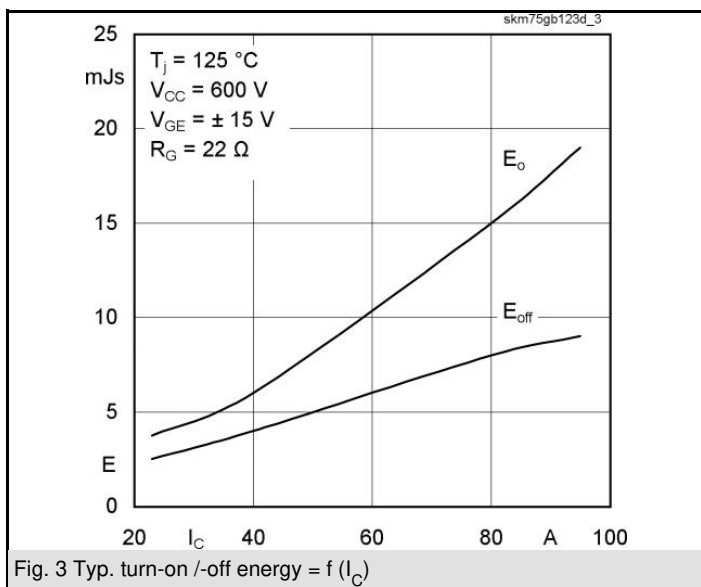
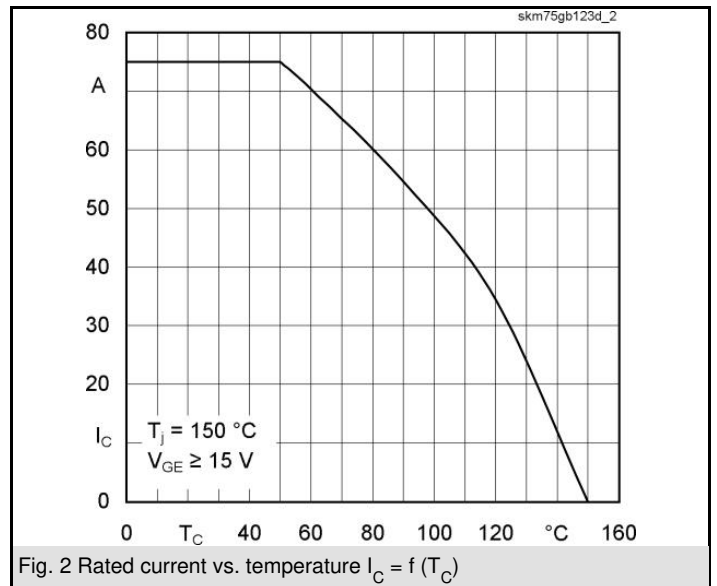
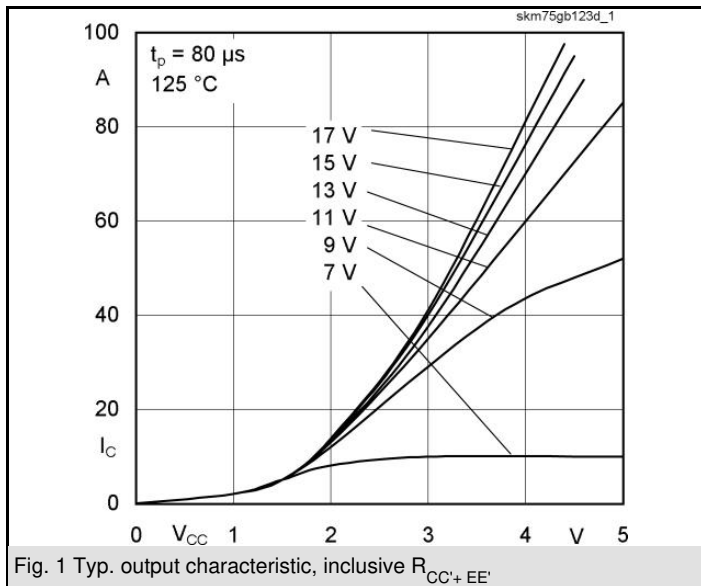
$Z_{th}$		Conditions	Values	Units
<b><math>Z_{th(j-c)I}</math></b>				
$R_{\theta j-c}$	$i = 1$		180	mk/W
$R_{\theta j-c}$	$i = 2$		64	mk/W
$R_{\theta j-c}$	$i = 3$		22	mk/W
$R_{\theta j-c}$	$i = 4$		4	mk/W
$\tau_{th(j-c)}$	$i = 1$		0,0327	s
$\tau_{th(j-c)}$	$i = 2$		0,0479	s
$\tau_{th(j-c)}$	$i = 3$		0,008	s
$\tau_{th(j-c)}$	$i = 4$		0,005	s
<b><math>Z_{th(j-c)D}</math></b>				
$R_{\theta j-cD}$	$i = 1$		380	mk/W
$R_{\theta j-cD}$	$i = 2$		190	mk/W
$R_{\theta j-cD}$	$i = 3$		26	mk/W
$R_{\theta j-cD}$	$i = 4$		4	mk/W
$\tau_{th(j-c)D}$	$i = 1$		0,0947	s
$\tau_{th(j-c)D}$	$i = 2$		0,006	s
$\tau_{th(j-c)D}$	$i = 3$		0,08	s
$\tau_{th(j-c)D}$	$i = 4$		0,003	s

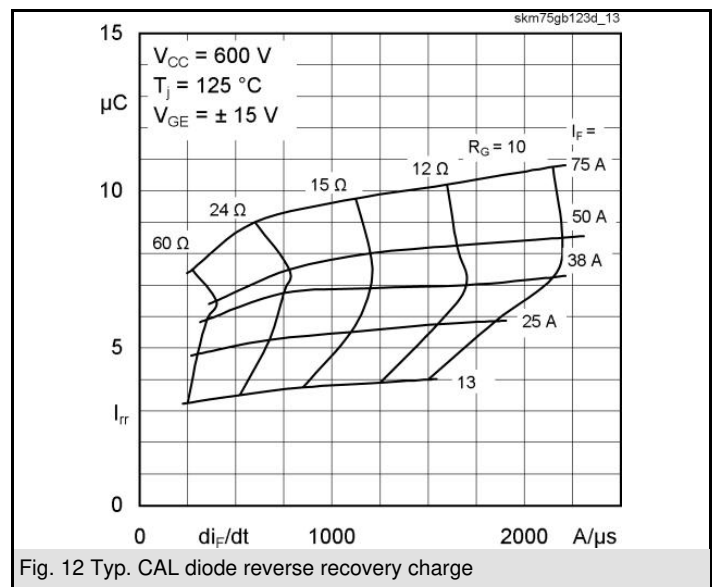
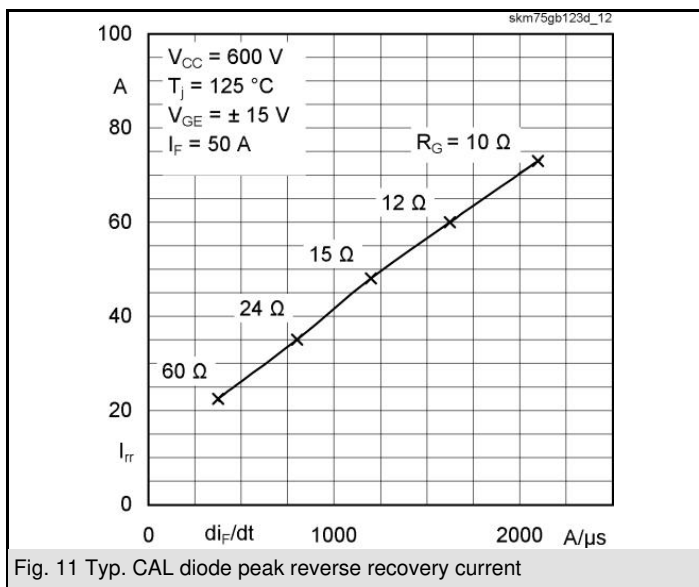
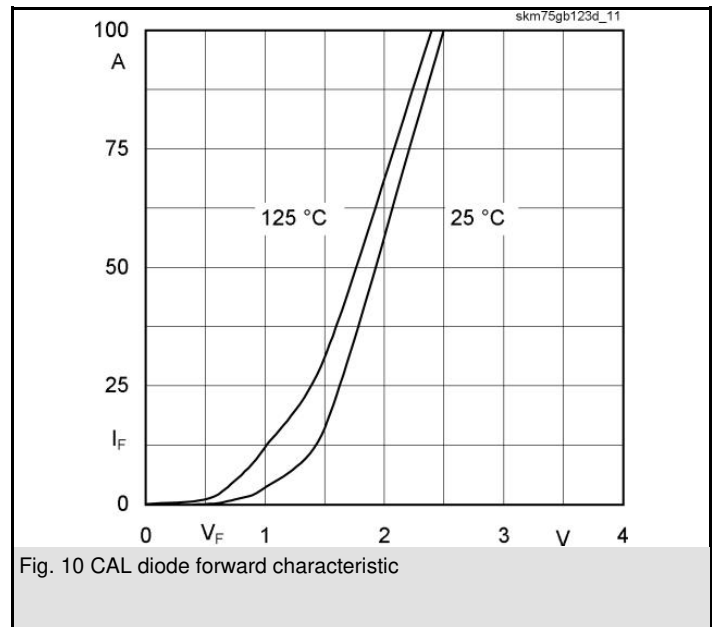
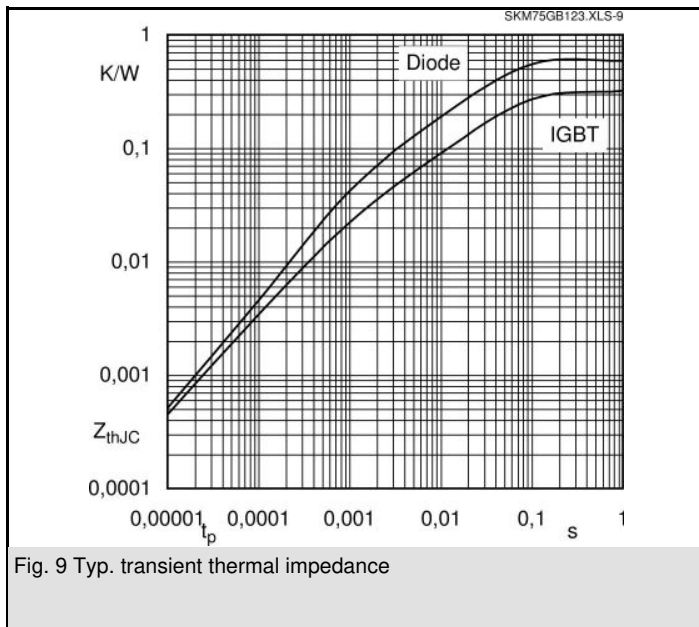
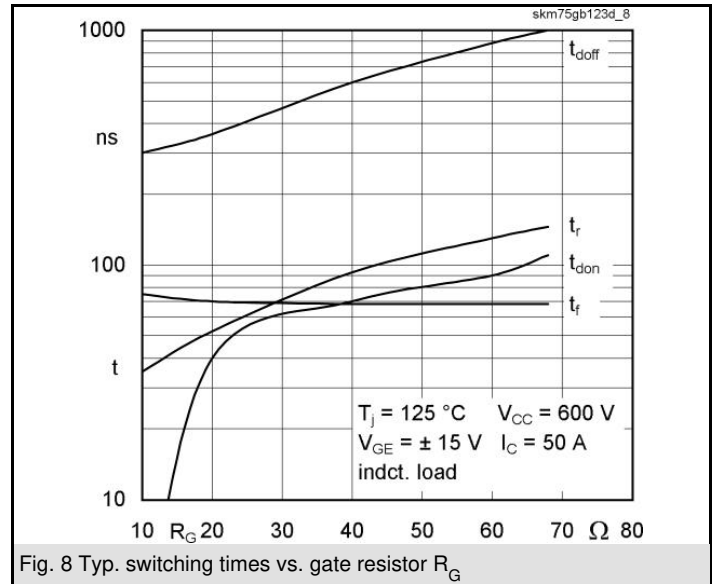
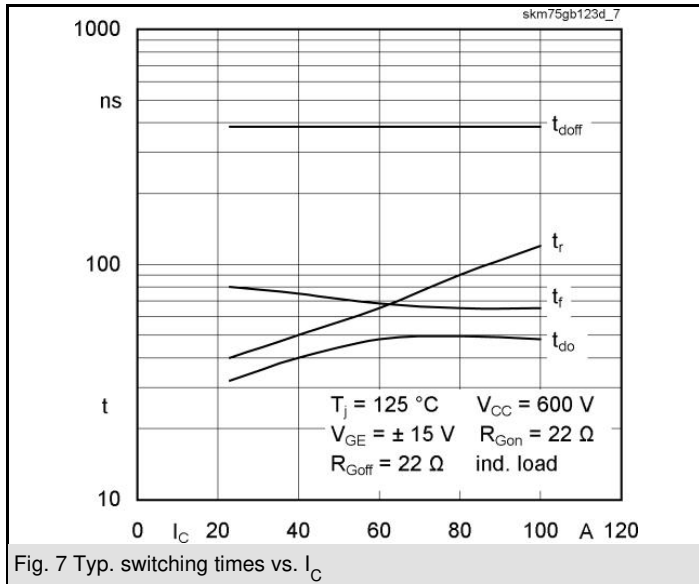


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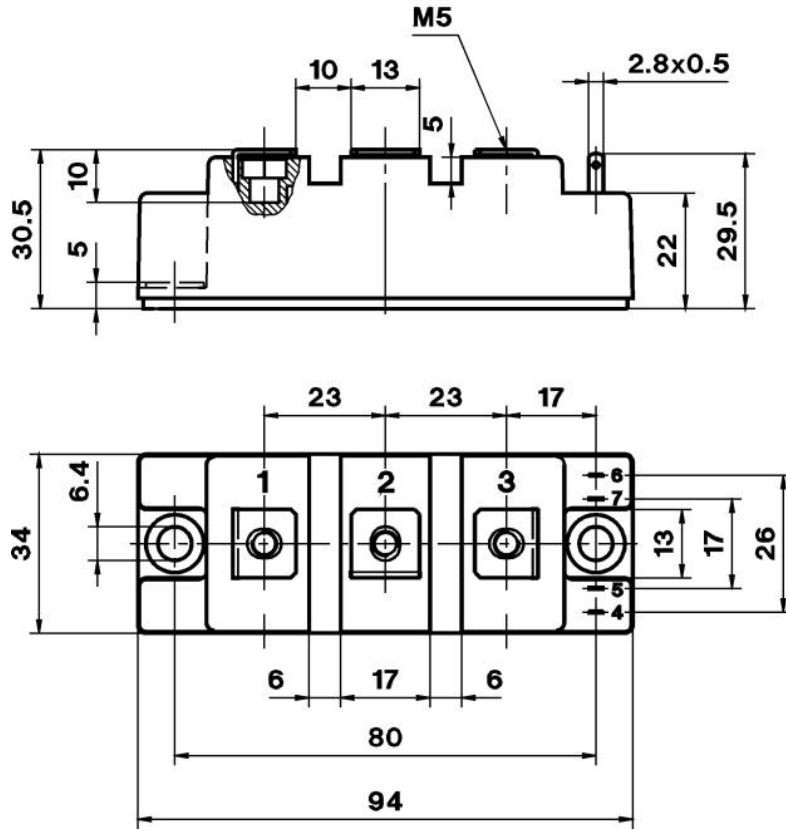


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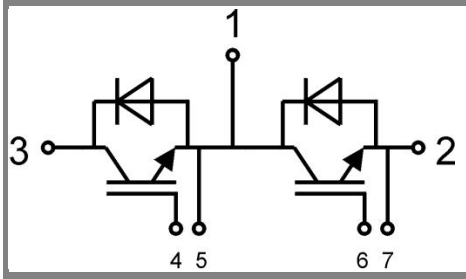
UL Recognized

CASED61

File 63 532



Case D 61



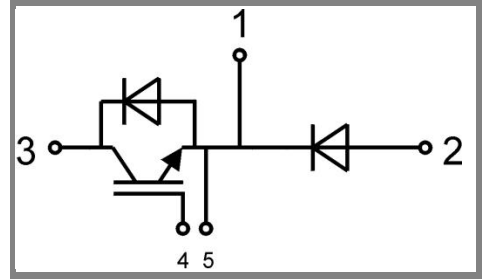
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Case D 61



GAL

Case D 62 (→ D 61)



GAR

Case D 63 (→ D 61)